

Amendments to the Claims

This listing of Claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1 - 16 (cancelled).

Claim 17 (currently amended): A structure of a LED device, the structure comprising:

a LED substrate having ~~an uppermost~~ a GaP layer thereon; and
a liquid phase epitaxy grown transparent layer having Zn dopants therein on said ~~uppermost~~ GaP layer of said LED substrate, wherein said transparent layer is composed of a semiconductor compound different to that of said ~~uppermost~~ GaP layer.

Claim 18 (canceled).

Claim 19 (currently amended): The structure according to claim 17, wherein said ~~transparent layer is formed by liquid phase epitaxy process~~ utilizing utilizes a supersaturated solution comprising metallic antimony (Sb) and indium (In) as a solvent.

Claim 20 (currently amended): The structure according to claim 18, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a supersaturated solution in the liquid phase epitaxy ~~LPE~~ process.

Claim 21 (currently amended): The structure according to claim 19, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the supersaturated solution in the liquid phase epitaxy ~~LPE~~ process.

Claim 22 (currently amended): A structure of a LED device, the structure comprising:
a LED substrate having ~~an uppermost~~ a GaP layer thereon; and
an non-GaP transparent layer having Zn dopants therein on said ~~uppermost~~ GaP layer formed by a ~~LPE~~ liquid phase epitaxy process using a supersaturated solution.

Claim 23 (currently amended): The structure according to claim 22, wherein said non-GaP transparent layer is formed by ~~LPE~~ liquid phase epitaxy process utilizing a supersaturated solution comprising metallic antimony (Sb) and indium (In) as a solvent.

Claim 24 (currently amended): The structure according to claim 22, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a supersaturated solution in the ~~LPE~~ liquid phase epitaxy process.

Claim 25 (currently amended): The structure according to claim 22, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the supersaturated solution in the ~~LPE~~ liquid phase epitaxy process.